

# 2SC495

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SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

9097250 TOSHIBA (DISCRETE/OPTO)

56C 07407 0 T-29-23

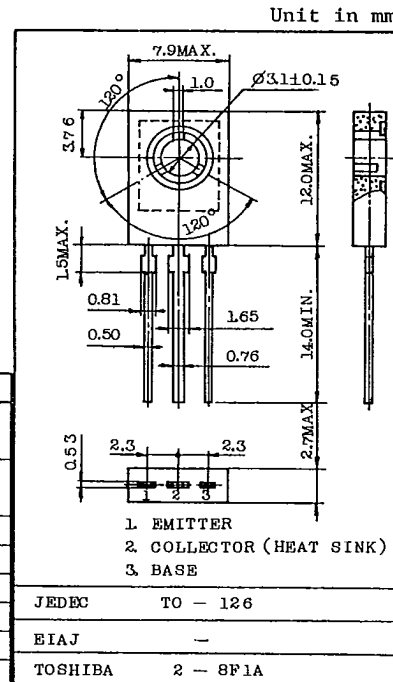
MEDIUM POWER AMPLIFIER APPLICATIONS.

## FEATURES:

- Low Collector Saturation Voltage  
:  $V_{CE(sat)}=0.25V$  (Typ.)
- 0.5 ~ 2 Watts Output Application.
- Complementary to 2SA505 and 2SA496.

MAXIMUM RATINGS ( $T_a=25^\circ C$ )

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	2SC495	70	V
	2SC496	40	
Collector-Emitter Voltage	2SC495	50	V
	2SC496	30	
Emitter-Base Voltage	$V_{EBO}$	5	V
Collector Current	$I_C$	1	A
Emitter Current	$I_E$	-1	A
Collector Power Dissipation	$P_C$	1	W
Junction Temperature	$T_j$	150	$^\circ C$
Storage Temperature Range	$T_{stg}$	-55 ~ 150	$^\circ C$



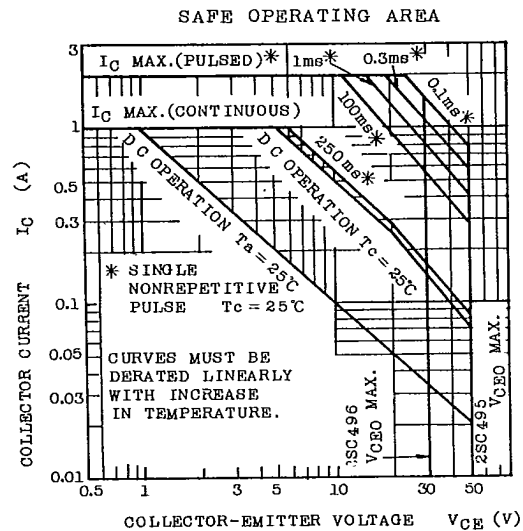
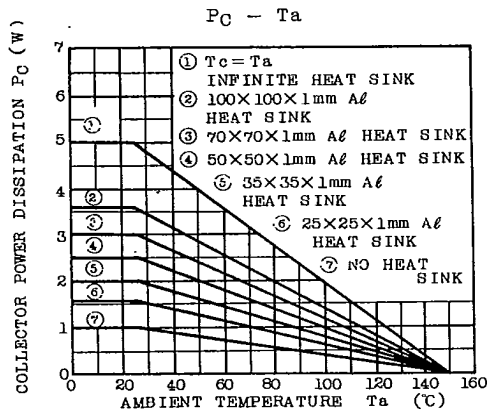
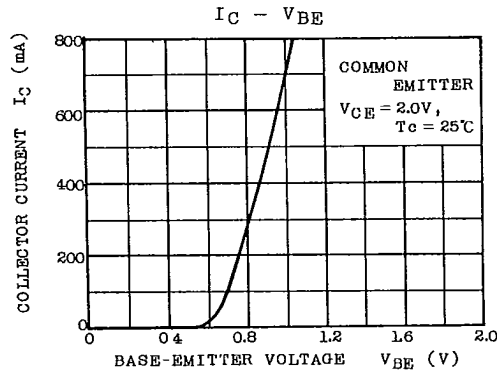
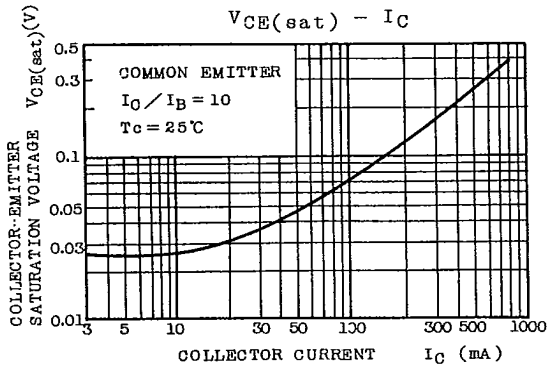
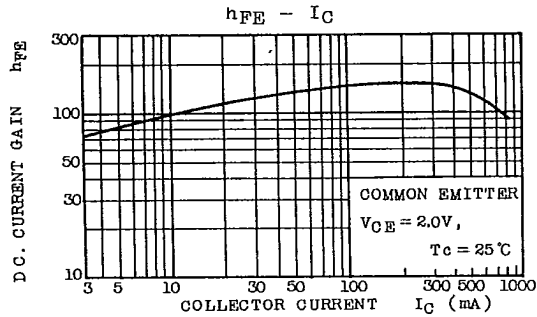
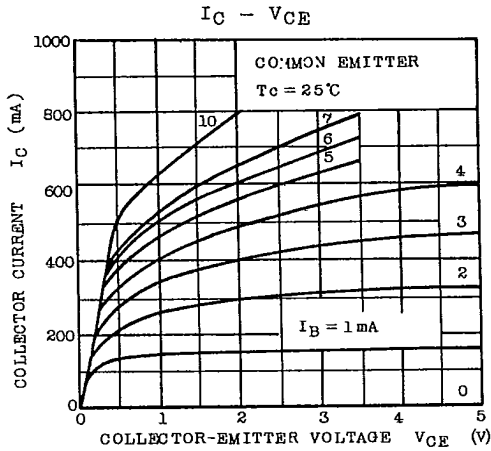
Mounting Kit No. AC46C  
Weight : 0.72g

ELECTRICAL CHARACTERISTICS ( $T_a=25^\circ C$ )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	$I_{CBO}$	$V_{CB}=30V, I_E=0$	-	-	1.0	$\mu A$
Emitter Cut-off Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$	-	-	1.0	$\mu A$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=10mA, I_B=0$	50	-	-	V
			30	-	-	
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	5	-	-	V
DC Current Gain	$h_{FE(1)}$ (Note)	$V_{CE}=2V, I_C=50mA$	40	-	240	
			$h_{FE(2)}$	$V_{CE}=2V, I_C=800mA$	13	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=500mA, I_B=50mA$	-	0.25	0.8	V
Base-Emitter Voltage	$V_{BE}$	$V_{CE}=2V, I_C=500mA$	-	0.9	1.1	V
Transition Frequency	$f_T$	$V_{CE}=10V, I_C=10mA$	50	100	-	MHz
Collector Output Capacitance	$C_{ob}$	$V_{CB}=10V, I_E=0, f=1MHz$	-	10	-	pF

Note :  $h_{FE(1)}$  Classification R : 40~80, O : 70~140, Y : 120~240

TOSHIBA CORPORATION



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